VS-10RIA Series

Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 10 A



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PRODUCT SUMMARY				
Package	TO-208AA (TO-48)			
Diode variation Single SCR				
I _{T(AV)}	10 A			
V _{DRM} /V _{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000V, 1200 V			
V _{TM}	1.75 V			
I _{GT}	60 mA			
TJ	-65 °C to +125 °C			

FEATURES

- Improved glass passivation for high reliability and exceptional stability at high temperature
- High dI_F/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I		10	А			
I _{T(AV)}	T _C	85	°C			
I _{T(RMS)}		25	А			
1	50 Hz	225	Δ			
ITSM	60 Hz	240	A			
l ² t	50 Hz	255	A ² s			
1-1	60 Hz	233	— A ² S			
V _{DRM} /V _{RRM}		100 to 1200	V			
t _q	Typical	110	μs			
TJ		-65 to +125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAG	VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	I _{DRM} /I _{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA				
	10	100	150	20				
	20	200	300					
	40	400	500					
VS-10RIA	60	600	700	10				
	80	800	900	10				
	100	1000	1100					
	120	1200	1300					

Notes

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

⁽²⁾ For voltage pulses with $t_p \le 5$ ms

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ABSOLUTE MAXIMUM RAT	TINGS						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS	
Maximum average on-state current	I _{T(AV)}	180° conducti	180° conduction, half sine wave			А	
at case temperature	· 1(AV)				85	°C	
Maximum RMS on-state current	I _{T(RMS)}				25	Α	
		t = 10 ms	No voltage		225		
Maximum peak, one-cycle	la su c	t = 8.3 ms	reapplied		240	А	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		190	^	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	200		
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	255	A ² s	
		t = 8.3 ms			233		
		t = 10 ms	100 % V _{BBM}		180		
		t = 8.3 ms	reapplied		165		
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10 m	ns, no voltage reap	plied	2550	A²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x	$I_{T(AV)} < I < \pi \times I_{T(AV)}$), T _J = T _J maximum	1.10	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}),$	T _J = T _J maximum		1.39	v	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x	(16.7 % x π x I _{T(AV)} < I < π x I _{T(AV)}), T _J = T _J maximum			mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			16.7	11152	
Maximum on-state voltage	V _{TM}	I_{pk} = 32 A, T _J = 25 °C, t _p = 10 ms sine pulse			1.75	V	
Maximum holding current	Ι _Η	$T = 25 \circ C$ on	odo oupply 12 V ro	vojetivo lood	130	m۸	
Typical latching current	١L	$1_{\rm J} = 25$ C, and	ode supply 12 V re		200	mA	

SWITCHING					
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS
	$V_{DRM} \le 600 \text{ V}$			200	
Maximum rate of rise	$V_{DRM} \le 800 \text{ V}$	dl⊧/dt	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$	180	A/µs
of turned-on current $V_{DRM} \le 1$	$V_{DRM} \le 1000 \text{ V}$	ui _F /ui	dI _F /dt Gate pulse = 20 V, 15 Ω , t _p = 6 µs, t _r = 0.1 µs maximum I _{TM} = (2 x rated dI/dt) A	160	
V _{DRM} ≤ 1600				150	
Typical turn-on time		t _{gt}	T_J = 25 °C, at rated V_{DRM}/V_{RRM} , T_J = 125 °C	0.9	
Typical reverse recover	ery time	t _{rr}	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}, t_p > 200 \ \mu s, \ dI_F/dt = -10 \ A/\mu s$	4	μs
Typical turn-off time		tq	$T_J=T_J$ maximum, I_{TM} = $I_{T(AV)},t_p>200~\mu s,V_R$ = 100 V, dI_F/dt = - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W	110	μu

Note

• $t_q = 10 \ \mu s$ up to 600 V, $t_q = 30 \ \mu s$ up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	100	V/µs
of off-state voltage	uv/ut	$T_J = T_J$ maximum linear to 67 % rated V_{DRM}		v/µs

Note

 $^{(1)}$ Available with: dV/dt = 1000 V/µs, to complete code add S90 i.e. 10RIA120S90

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TRIGGERING					
PARAMETER	SYMBOL	TE	EST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			8.0	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J maximum$		2.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum		1.5	А
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J maximum$		10	V
		T _J = -65 °C		90	mA
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger	60	
		T _J = 125 °C	current/voltage are the lowest value	35	
		T _J = -65 °C	which will trigger all units 6 V anode	3.0	V
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	to cathode applied	2.0	
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated value		2.0	mA
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum, V _{DRM} = Rated value	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES		
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-65 to	-65 to +125		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.85		K/W	
Maximum thermal resistance, case to heat sink	R _{thCS}	CS Mounting surface, smooth, flat and greased 0.35		35	rv vv	
			TO NUT	TO DEVICE		
			20 (27.5)	25	lbf · in	
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf ∙ m	
			2.3 (3.1)	2.8	N·m	
Approvimeto weight			1	4	g	
Approximate weight			0.	49	oz.	
Case style		See dimensions - link at the end of datasheet	TC	-208AA (TO-4	8)	

	I			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.44	0.32		
120°	0.53	0.56		
90°	0.68	0.75	$T_J = T_J maximum$	K/W
60°	1.01	1.05		
30°	1.71	1.73		

Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

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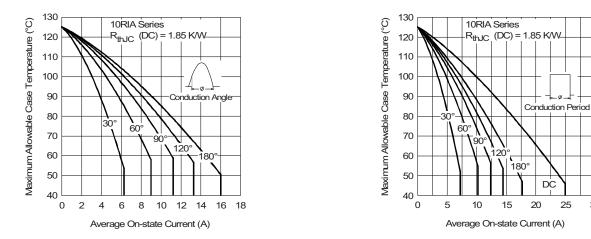


Fig. 1 - Current Ratings Characteristics

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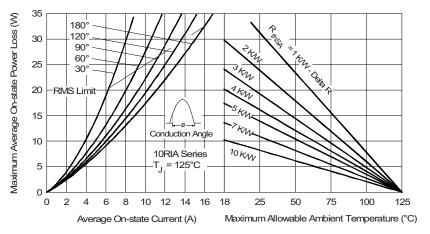
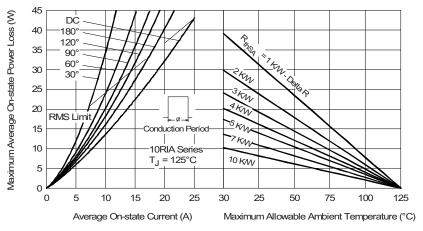
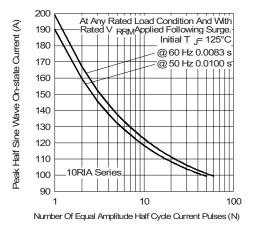


Fig. 3 - On-State Power Loss Characteristics





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Fig. 5 - Maximum Non-Repetitive Surge Current

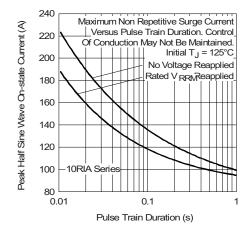
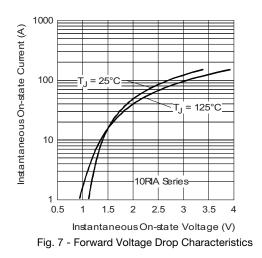


Fig. 6 - Maximum Non-Repetitive Surge Current



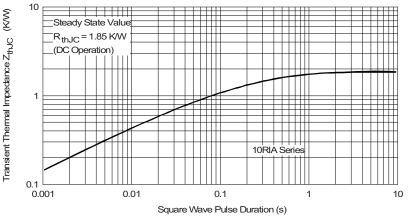


Fig. 8 - Thermal Impedance $Z_{thJC} \mbox{ Characteristics}$

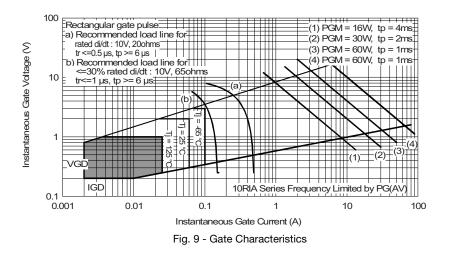
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ORDERING INFORMATION TABLE

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SHA

Device code	VS-	10	RIA	120	М	S90	
	1	2	3	4	5	6	
	1 - 2 - 3 - 4 - 5 -	Cur Ess Vol Nor	rent coo ential p tage coo ne = Stu	art numl de x 10 :	ber = V _{RRM} TO-2084	(see Vo AA (TO-	ltage Ratings table) 48) 1/4" 28UNF-2A M6 x 1
	6 -	Nor		dt:) V/µs (s) V/µs (s		-)

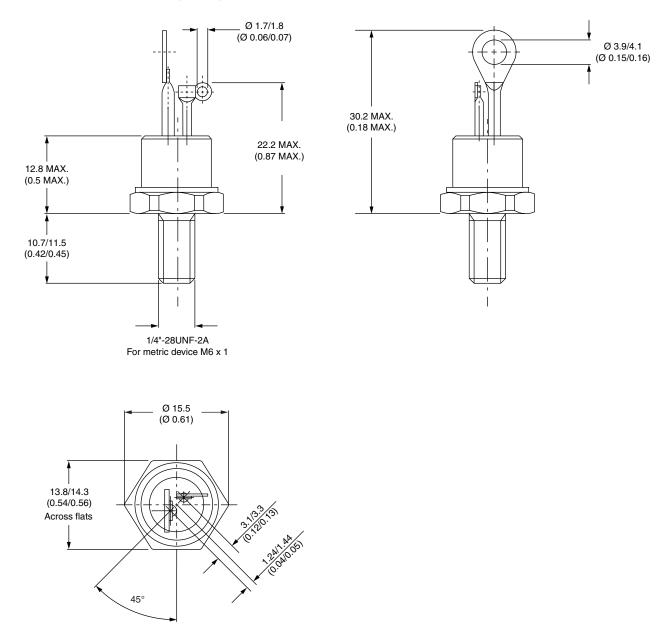
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95333			

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TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)





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